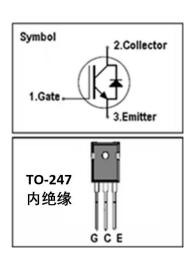
IGBT

Features

- 1200V,15A
- V_{CE(sat)(typ.)}=1.75V@V_{GE}=15V,I_C=15A
- Positive temperature coefficient
- Fast Switching
- Reliable and Rugged
- Halogen Free and Green Devices Available



JIAEN Trench IGBTs offer lower losses and higher energy efficiency for application such as UPS, Motor drives, PFC, Portable power station and other soft switching applications.



Absolute Maximum Ratings

Symbol	Parameter Value		Units	
Vces	Collector-Emitter Voltage	1200	V	
V _{GES}	Gate-Emitter Voltage	<u>+</u> 20	V	
	Continuous Collector Current (Tc=25 °C)	30	Α	
lc	Continuous Collector Current (Tc=100°C)	15	Α	
Ісм	Pulsed Collector Current (Note 1)	45	Α	
l _F	Diode Continuous Forward Current (T _C =100 °C)	15	A	
I _{FM}	Diode Maximum Forward Current (Note 1)	45	Α	
t _{sc}	Short Circuit Withstand Time	5	us	
P _D	Maximum Power Dissipation (T _C =25 °C)	175 W		
TJ	Operating Junction Temperature Range	-55 to +175 °C		

Thermal Characteristics

Symbol	Parameter	Max.	Units
R _{th j-c}	Thermal Resistance, Junction to case for IGBT	0.85	°C/ W
R _{th j-c}	Thermal Resistance, Junction to case for Diode	1.5	°C/ W
R _{th j-a}	Thermal Resistance, Junction to Ambient	40	°C/ W



$\underline{\textbf{Electrical Characteristics}} \ (\ \texttt{T}_{\texttt{C}} = 25 \text{ } \text{\'e} \texttt{C} \ \text{unless otherwise noted} \)$

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV _{CES}	Collector-Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 1mA	1200	-	-	V
I _{CES}	Collector-Emitter Leakage Current	V _{CE} = 1200V, V _{GE} = 0V	-	-	100	uA
I _{GES}	Gate Leakage Current, Forward	$V_{GE} = + 20V, V_{CE} = 0V$	-	-	<u>+</u> 200	nA
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_{C} = 1 \text{mA}$	5.0	-	7.0	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} =15V, I _C = 15A	-	1.75	-	V
Qg	Total Gate Charge	V _{CC} =600V V _{GE} =15V IC=15A	-	70	-	nC
t d(on)	Turn-on Delay Time		-	19	-	ns
t r	Turn-on Rise Time	V _{CC} =600V	-	20	-	ns
t d(off)	Turn-off Delay Time	V _{GE} =15V	-	131	-	ns
t f	Turn-off Fall Time	I _C =15A R _G =15Ω Inductive Load T _C =25 °C	-	210	-	ns
Eon	Turn-on Switching Loss		-	1.1	-	mJ
Eoff	Turn-off Switching Loss		-	0.9	-	mJ
Ets	Total Switching Loss		-	2.0	-	mJ
C _{ies}	Input Capacitance	V _{CE} =25V	-	1320	-	pF
Coes	Output Capacitance	V _{GE} =0V	-	57	-	pF
C _{res}	Reverse Transfer Capacitance	f = 1MHz	-	11	-	pF

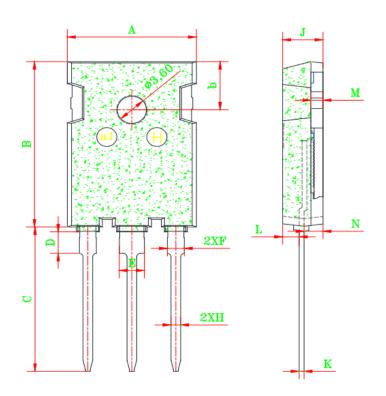
Electrical Characteristics of Diode (T_C=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
V _F	Diode Forward Voltage	I _F =15A	-	2.1	3.5	V
trr	Diode Reverse Recovery Time	V _{CE} = 600V	-	130	-	ns
Irr	Diode peak Reverse Recovery Current	I _F = 15A	-	4.8	-	Α
Qrr	Diode Reverse Recovery Charge	di _F /dt = 200A/us	-	220	=	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

TO-247 内绝缘 PACKAGE OUTLINE



	Dimensions			
Ref.	Millimeters			
	Min.	Тур.	Max.	
A	15. 70	16.00	16. 30	
b	6. 10	6. 30	6. 20	
В	20.70	21. 90	22. 10	
С	18.80	19. 10	19. 40	
D	2.64	2.84	3.04	
Е	2. 90	3. 10	3. 30	
F	1. 90	2. 10	2. 30	
G	5. 25	5. 45	5. 65	
Н	1. 10	1.20	1.30	
J	4. 90	5. 00	5. 10	
K	0. 55	0.60	0. 65	
L	1.85	2.00	2. 15	
M	1. 40	1.50	1.60	
N	2. 10	2. 30	2. 50	

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